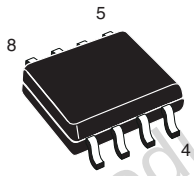
STS4DNFS30L

N-channel 30 V, 0.044 Ω, 4 A SO-8 STripFET™ MOSFET plus SCHOTTKY rectifier

Features

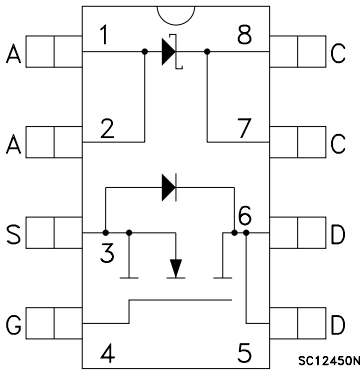
MOSFET	V_{DSS}	$R_{DS(on)}$	I_D
	30V	<0.056Ω	4A
SCHOTTKY	$I_{F(AV)}$	V_{RRM}	$V_{F(MAX)}$
	3A	30V	0.51V

- Standard outline for easy automated surface mount assembly
- Low threshold gate drive
- Integrated SCHOTTKY rectifier



S0-8

Figure 1. Internal schematic diagram



Applications

- Switching applications

Description

This device is an N-channel Power MOSFET. It associates the latest low voltage STripFET™ in N-channel version to a low drop Schottky diode. Such configuration is extremely versatile in implementing, a large variety of DC-DC converters for printers, portable equipment, and cellular phones.

Table 1. Device summary

Order code	Marking	Package	Packaging
STS4DNFS30L	4DFS30L	SO-8	Tape and reel

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (v_{gs} = 0)	30	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate- source voltage	±16	V
I_D	Drain current (continuous) at T_C = 25°C	4	A
I_D	Drain current (continuous) at T_C = 100°C	2.5	A
I_{DM} (1)	Drain current (pulsed)	16	A
P_{TOT}	Total dissipation at T_C = 25°C dual operation	2	W

1. Pulse width limited by safe operating area.

Table 3. Schottky absolute maximum ratings

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		20	A
$I_{F(AV)}$	Average forward current	TL=125°C δ=0.5	3	A
I_{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	tp = 2 µs F=1 kHz	1	A
I_{RSM}	Non repetitive peak reverse current	tp = 100 µs	1	A
dv/dt	Critical rate of rise of reverse voltage		10000	V/µs

Table 4. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal resistance junction-ambient MOSFET(1)	62.5	°C/W °C/W
T_J	Junction temperature	-55 to 150	°C
T_{stg}	Storage temperature range	-55 to 150	°C

1. Mounted on FR-4 board (steady state).

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero gate voltage Drain current (V_{GS} = 0)	V_{DS} = Max rating			1	µA
		V_{DS}=Max rating, T_C=125°C			10	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ±16V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 2A		0.044	0.055	Ω
		V_{GS} = 5V, I_D = 2A		0.051	0.065	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS}= 15V, I_D=2A		5		S
C_{iss}	Input capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		330		pF
C_{oss}	Output capacitance			90		pF
C_{rss}	Reverse transfer capacitance			40		pF
Q_g	Total gate charge	V_{DD} = 24V, I_D = 4A, V_{GS} = 5V		6.5	9	nC
Q_{gs}	Gate-source charge			3.6		nC
Q_{gd}	Gate-drain charge			2		nC

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5.

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}=15 V, I_D=2A, R_G=4.7Ω, V_{GS}=5V (see Figure 13)		11		ns
t_r	Rise time			100		ns
$t_{d(off)}$	Turn-off delay time	V_{DD}=15 V, I_D=2A, R_G=4.7Ω, V_{GS}=5V (see Figure 13)		25		ns
t_f	Fall time			22		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				4	A
I_{SDM} (1)	Source-drain current (pulsed)				16	A
V_{SD} (2)	Forward on voltage	I_{SD} = 4A, V_{GS} = 0			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 4A, V_{DD} = 15V di/dt = 100A/µs, T_j = 150°C (see Figure 15)		35 25 1.4		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

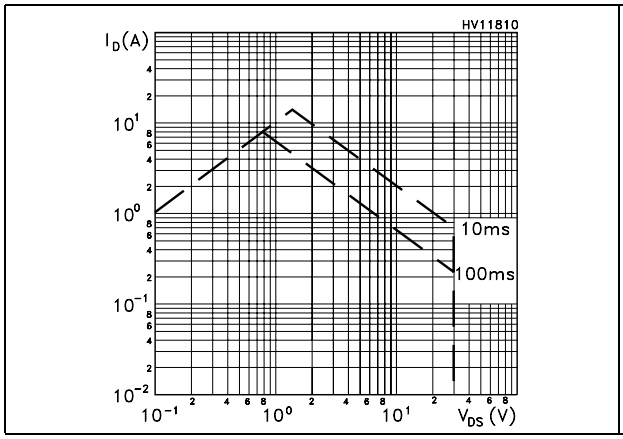


Figure 3. Thermal impedance

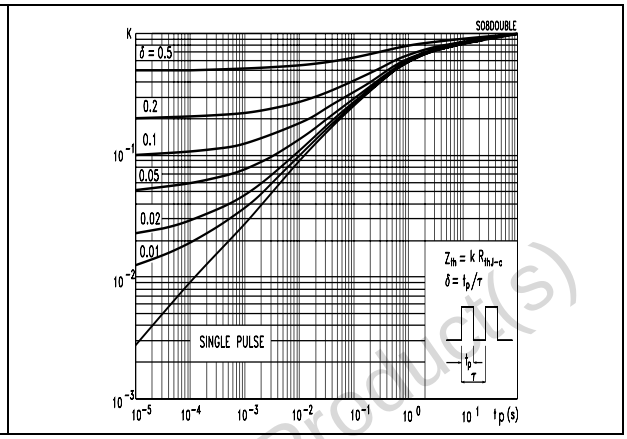


Figure 4. Output characteristics

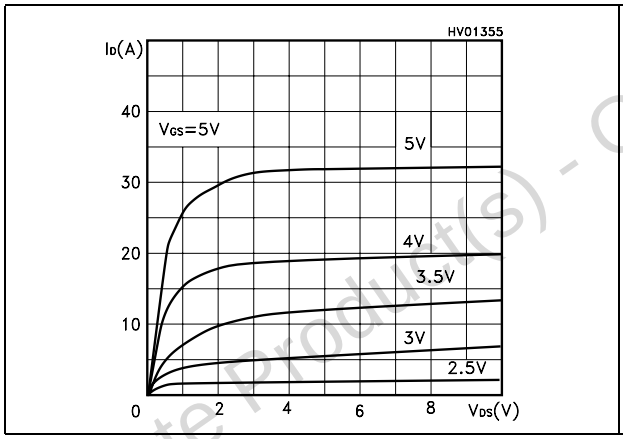


Figure 5. Transfer characteristics

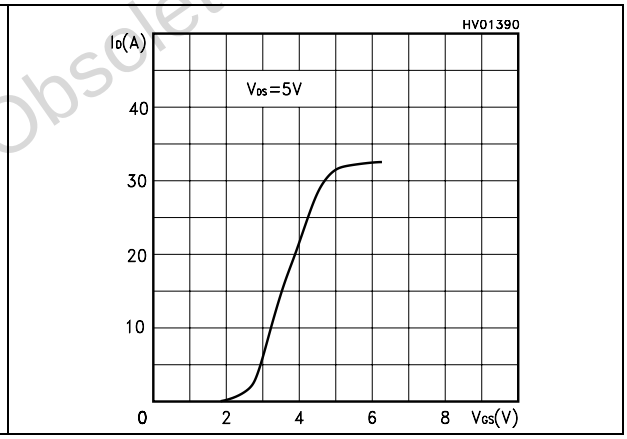


Figure 6. Transconductance

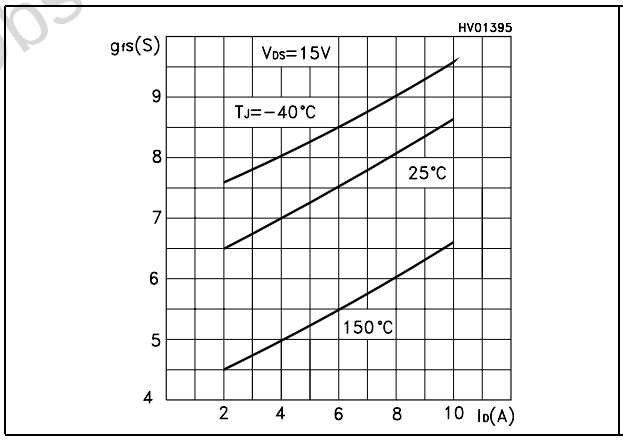


Figure 7. Static drain-source on resistance

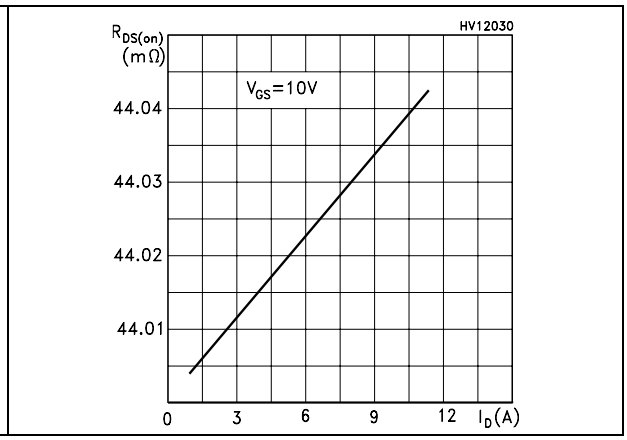


Figure 8. Gate charge vs. gate-source voltage

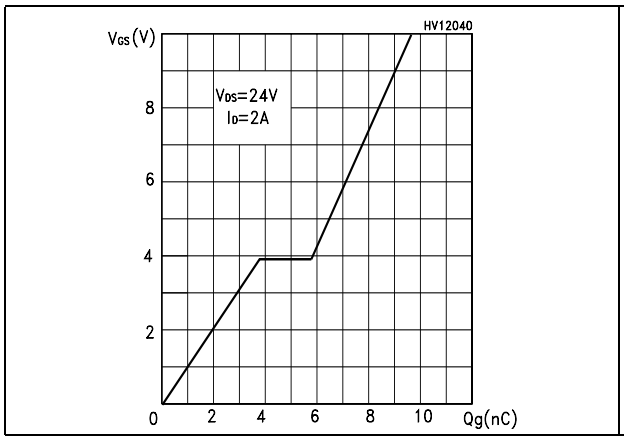


Figure 9. Capacitance variations

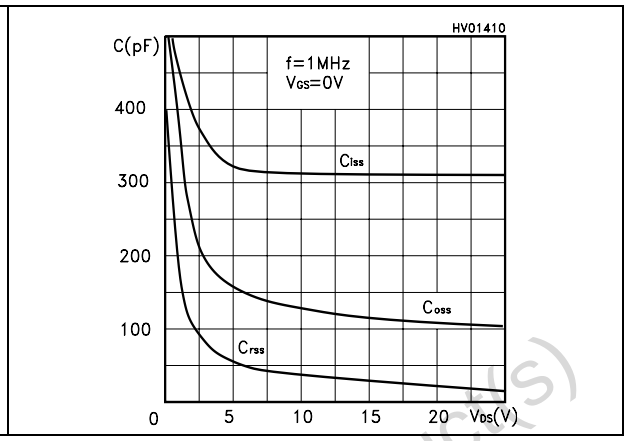


Figure 10. Normalized gate threshold voltage vs. temperature

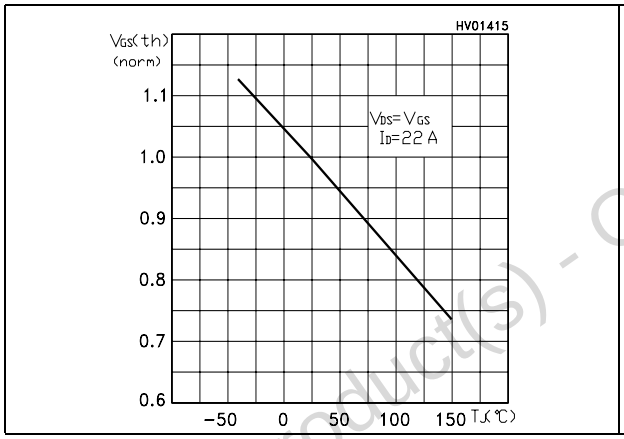


Figure 11. Normalized on resistance vs. temperature

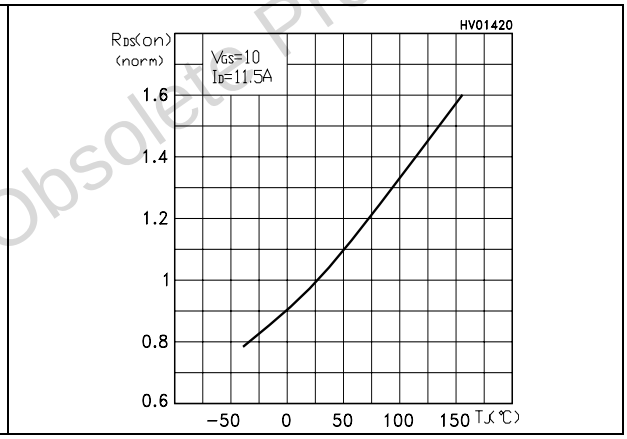
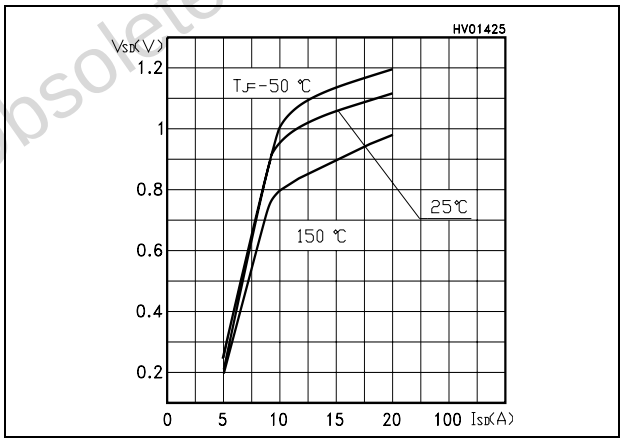


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Switching times test circuit for resistive load

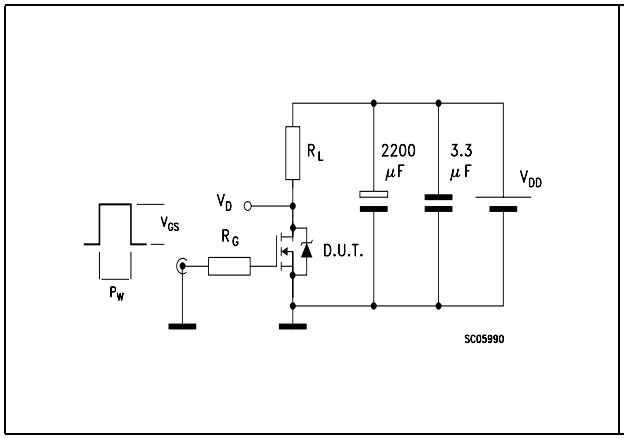


Figure 14. Gate charge test circuit

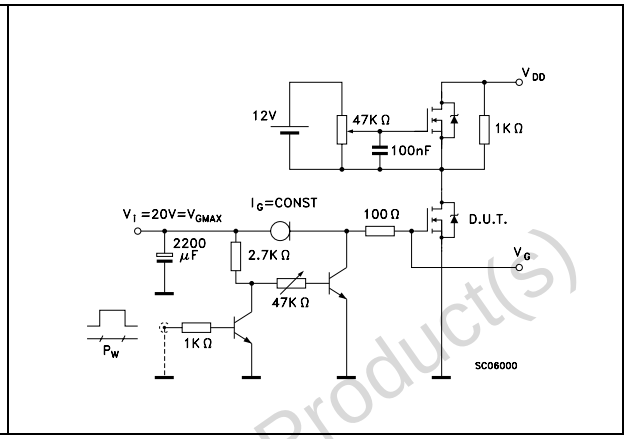


Figure 15. Test circuit for inductive load switching and diode recovery times

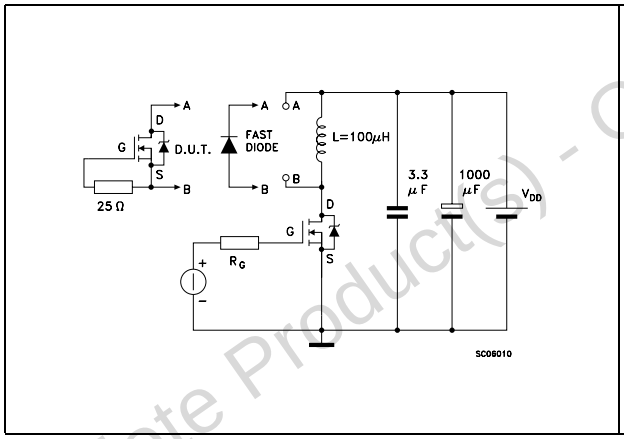


Figure 16. Unclamped Inductive load test circuit

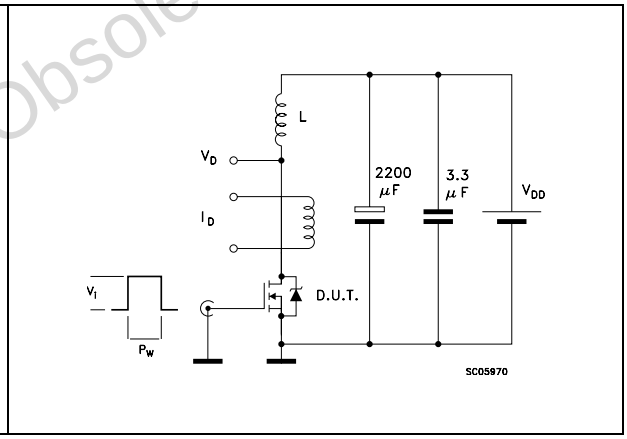


Figure 17. Unclamped inductive waveform

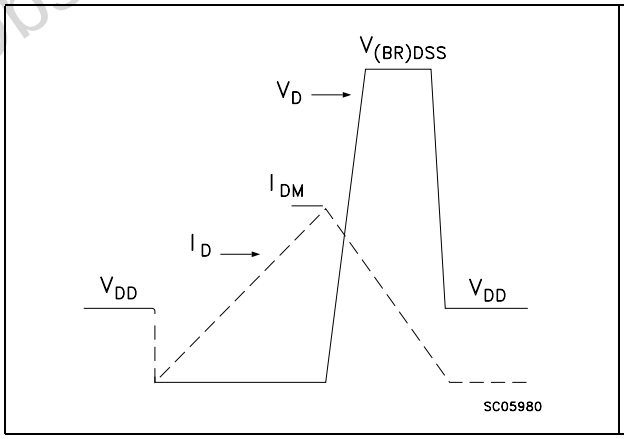
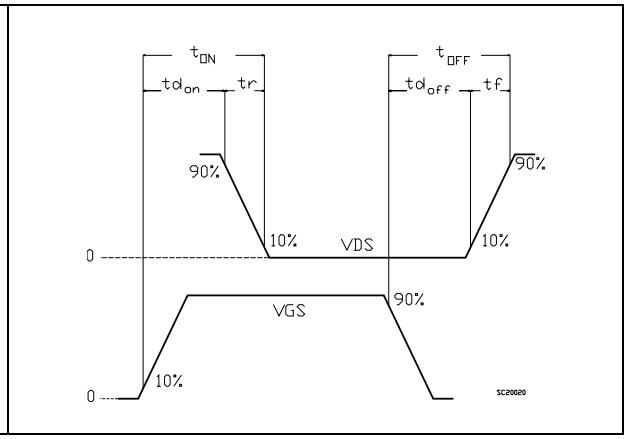


Figure 18. Switching time waveform



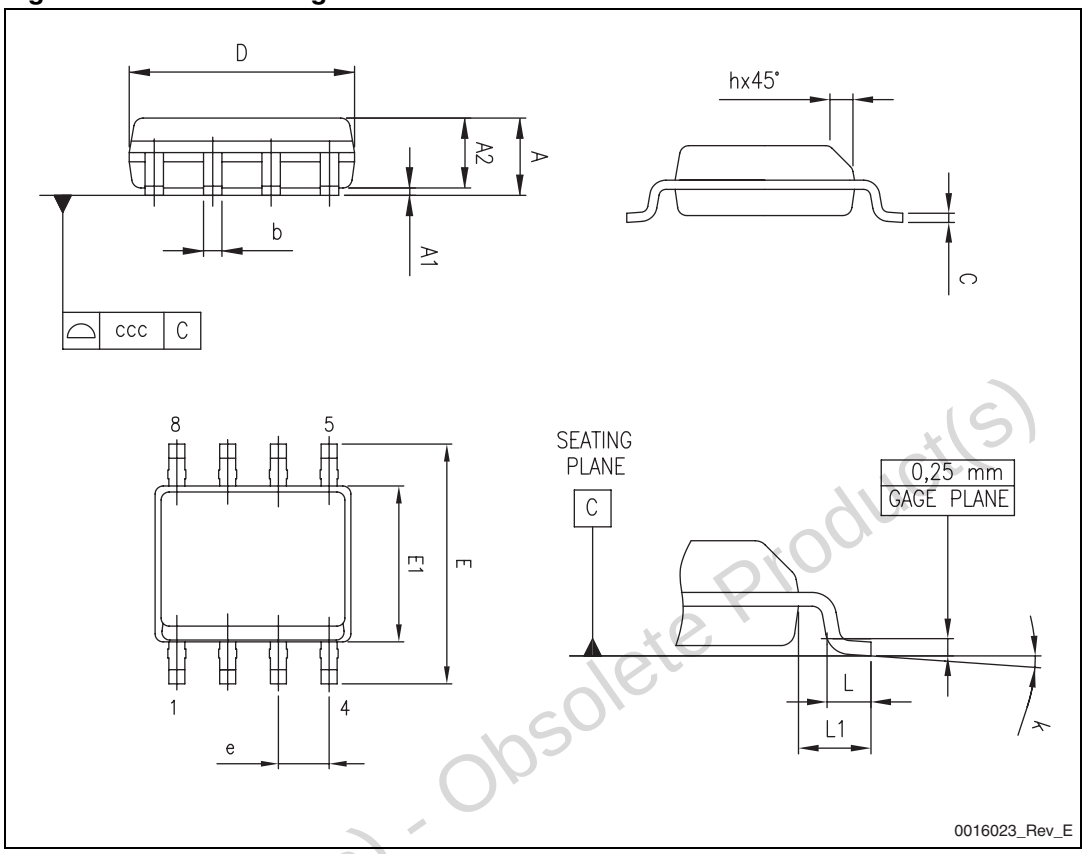
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. SO-8 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.28		0.48
c	0.17		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
k	0°		8°
ccc			0.10

Figure 19. SO-8 drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
21-Jun-2004	2	Complete version
10-Nov-2006	3	The document has been reformatted
26-Jan-2007	4	Typo mistakes on *Table 2*.
29-Jun-2011	5	Modified marking in *Table 1*. Updated mechanical data.

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